YJ Planar Fast Recovery Diode Die Specification

600V 25A, Fast recovery diode die based on silicon planar process Part No.:LBDD5T600SS-330A

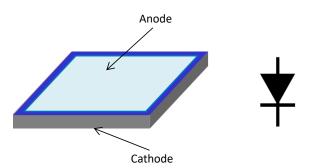
Main Products Characterstics

• Average forward current: IF(AV) = 25A

• Maximum operating junction temperature: Tj = 150 °C

Planar Construction

• Top metal: Ag



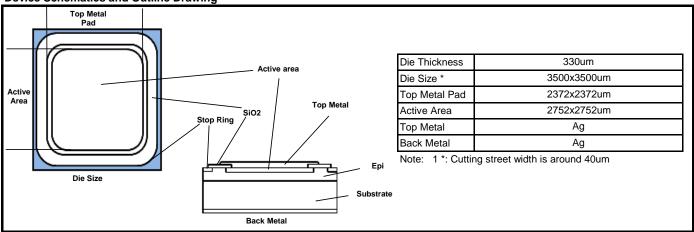
Maximum Ratings

Parameter	Symbol	Rating			
Repetitive peak reverse voltage	V_{RRM}	600V			
Average forward current	I _{F(AV)}	25A			
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	400A			
Storage temperature range	T _{stg}	-40 to +150 °C			
Maximum operating junction temperature	T _j	150 °C			

Static Electrical Characteristics (Ta = 25°C)

Parameter \$	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 50$ uA	V_{BR}	680V	690V
Maximum forward voltage drop I_F = 12.5A, Pulse Test: tp = 380 $\mu s,~\delta \leqslant 2\%$	V_{F}	0.92V	0.89V
Reverse Recovery Time $I_F=0.5A$, $I_R=1A$, $I_{rr}=0.25A$	Trr	500ns	470ns
$\begin{aligned} &\text{Maximum reverse current} & \ V_{\text{R}} = V_{\text{RRM}} \\ &\text{Pulse Test: tp} = 10 \text{ ms}, \ \delta \leqslant 2\% \end{aligned}$	I _R	2uA	0.05uA

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.